

ELEC 402 – November 14, 2021

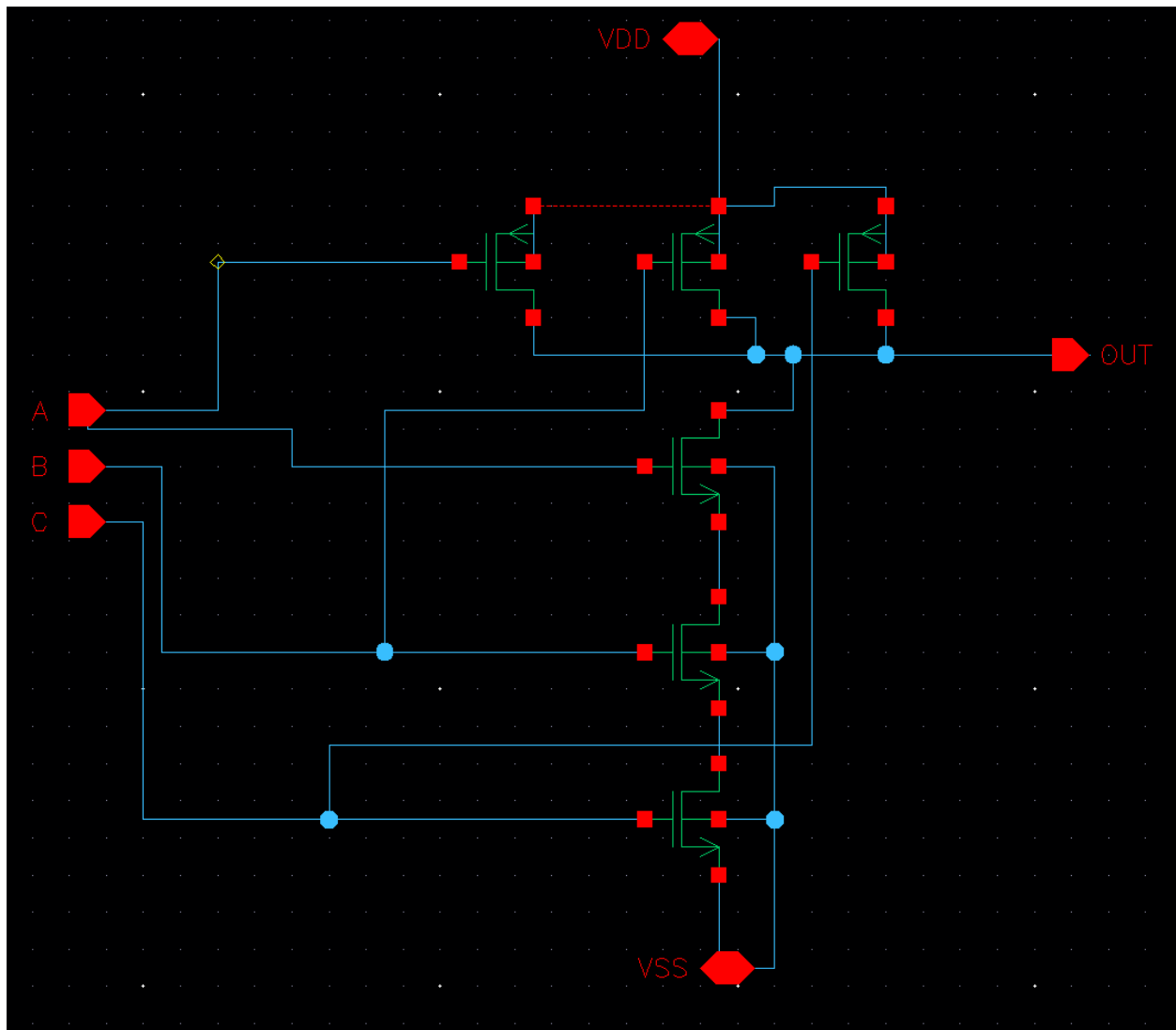
Project 4 Report

Martin Chua – 35713411

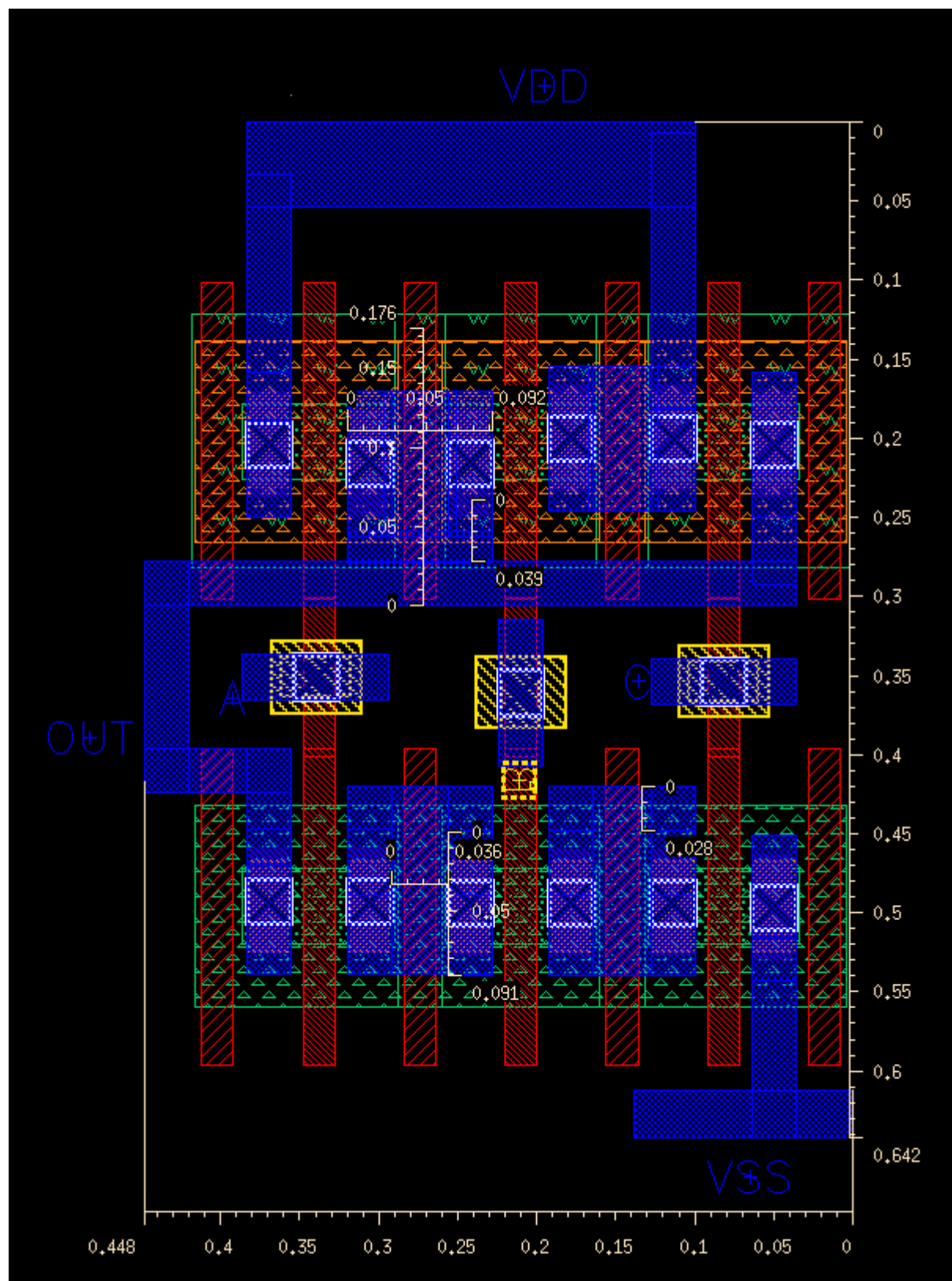
15nm FinFET

Area	Delay (avg)	Area X Delay
0.25978 μm^2	23.636ps	6.14 ps* μm^2

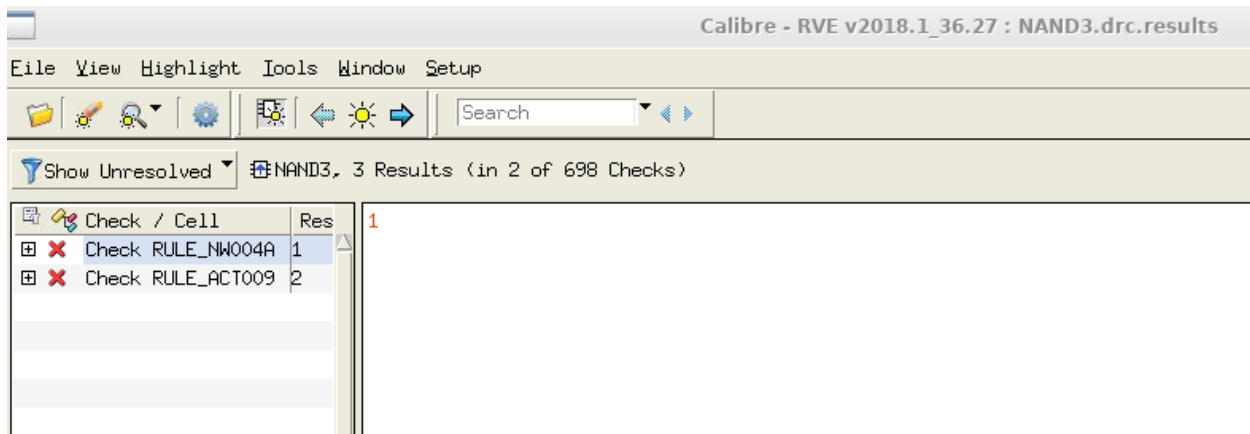
1. NAND3



NAND3 Schematic using default widths (2 fingers)



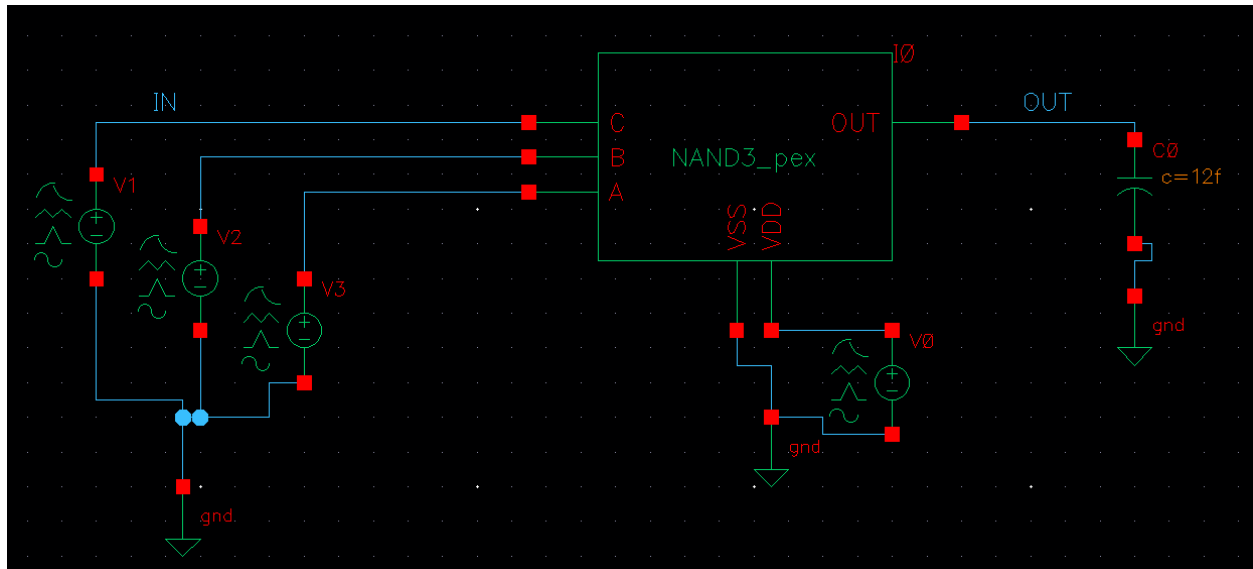
NAND3 Layout. Layout planned using the stick layout method / euler path taught in class, rather than directly translating from schematic to layout. In hindsight, it's possible to use 3 fingers for a two shared diffusion in the center.



DRC Results. DRC Summary can be found in Appendix A.



LVS Results pass! (Final LVS results in Appendix C)

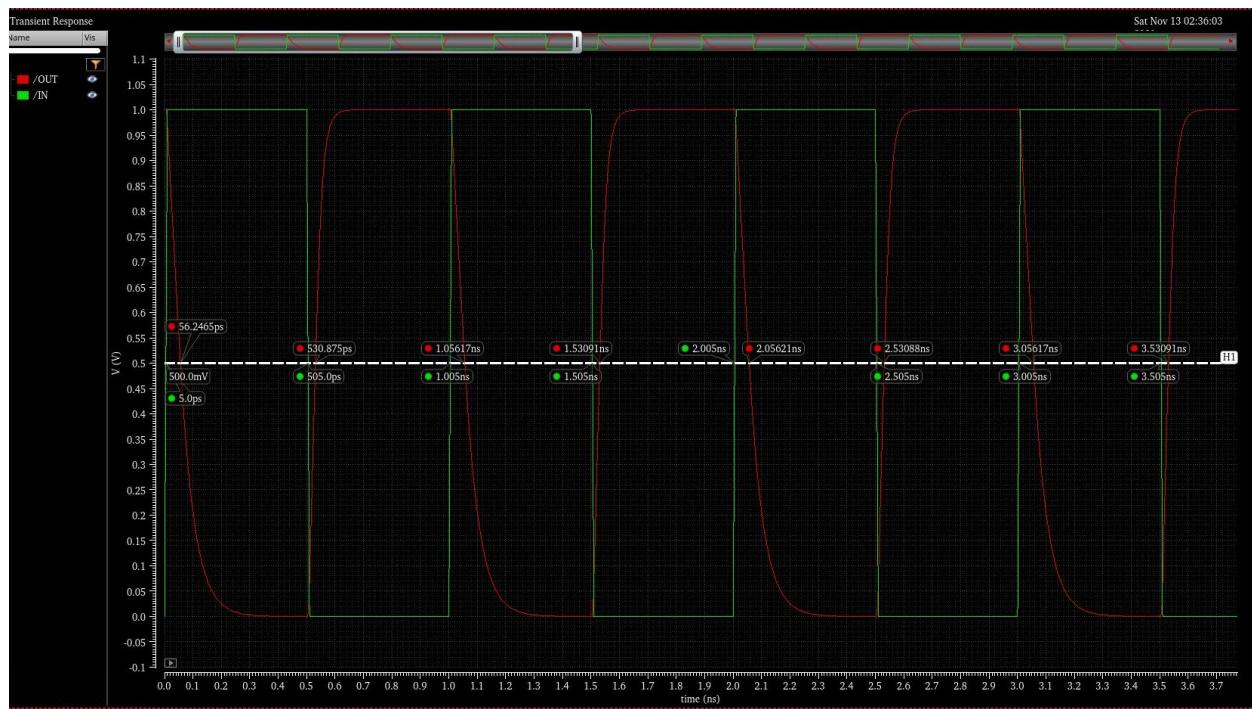


Worst case tau testbench schematic with 12 fF capacitor. V2 = V3 = VDD = 1 VDC. V1:

As seen in circuit schematic, worst case is when 1 transistor is off (pulled high) and others are on (pulled low) then the single transistor is also turned on (pulled low) and viceversa, aka 001 -> 000 -> 001. This is because all transistors are in series (pulldown) and parallel (pullup).

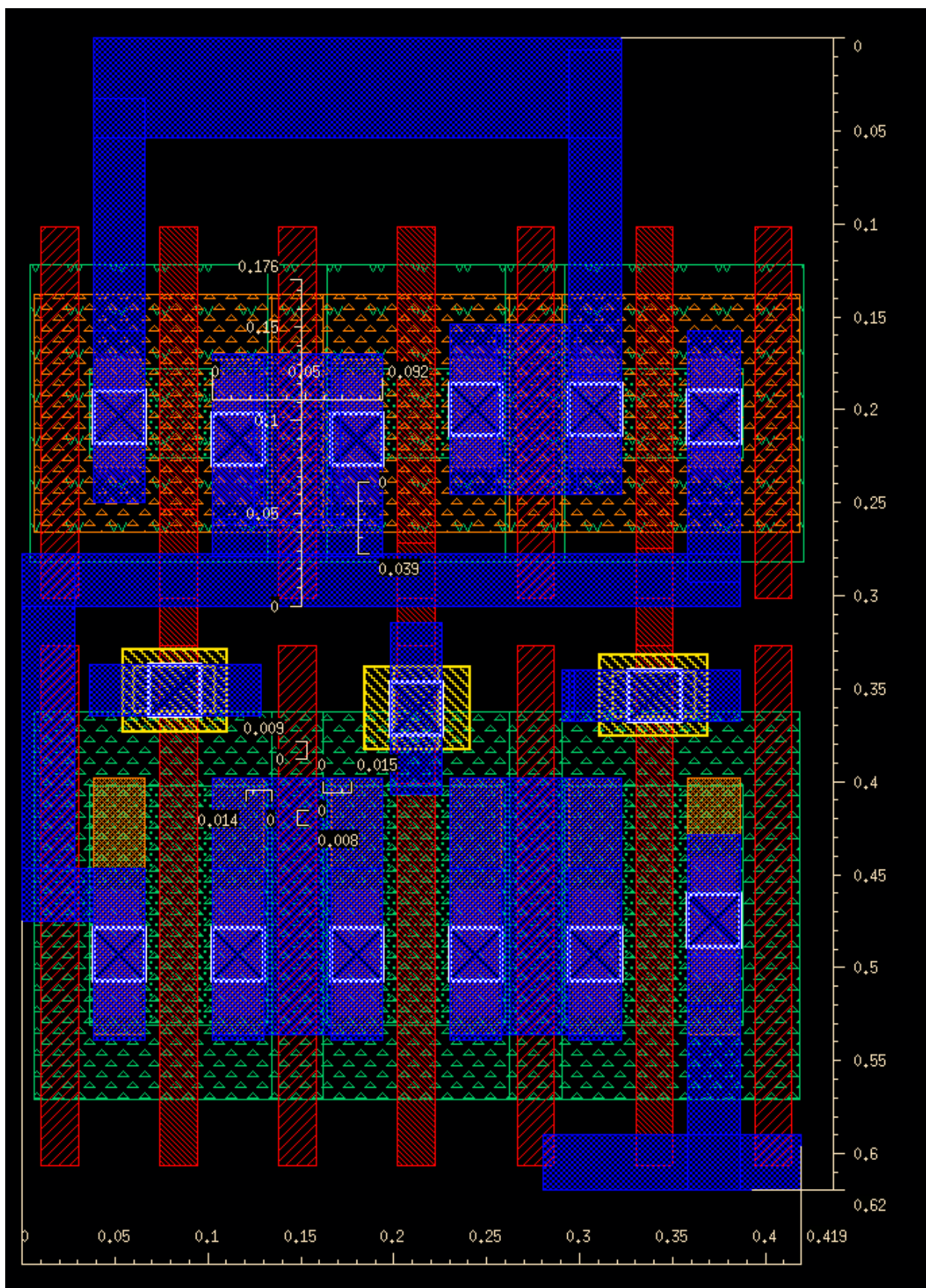
ivsignore	true
DC voltage	0 V
Source type	pulse
Frequency...	
Delay time	0 s
Zero value	0 V
One value	1 V
Period of ...	10n s
Rise time	10p s
Fall time	10p s
Type of rising...	

Rise and fall time is specified (slew rate) in the assignment as 10ps.

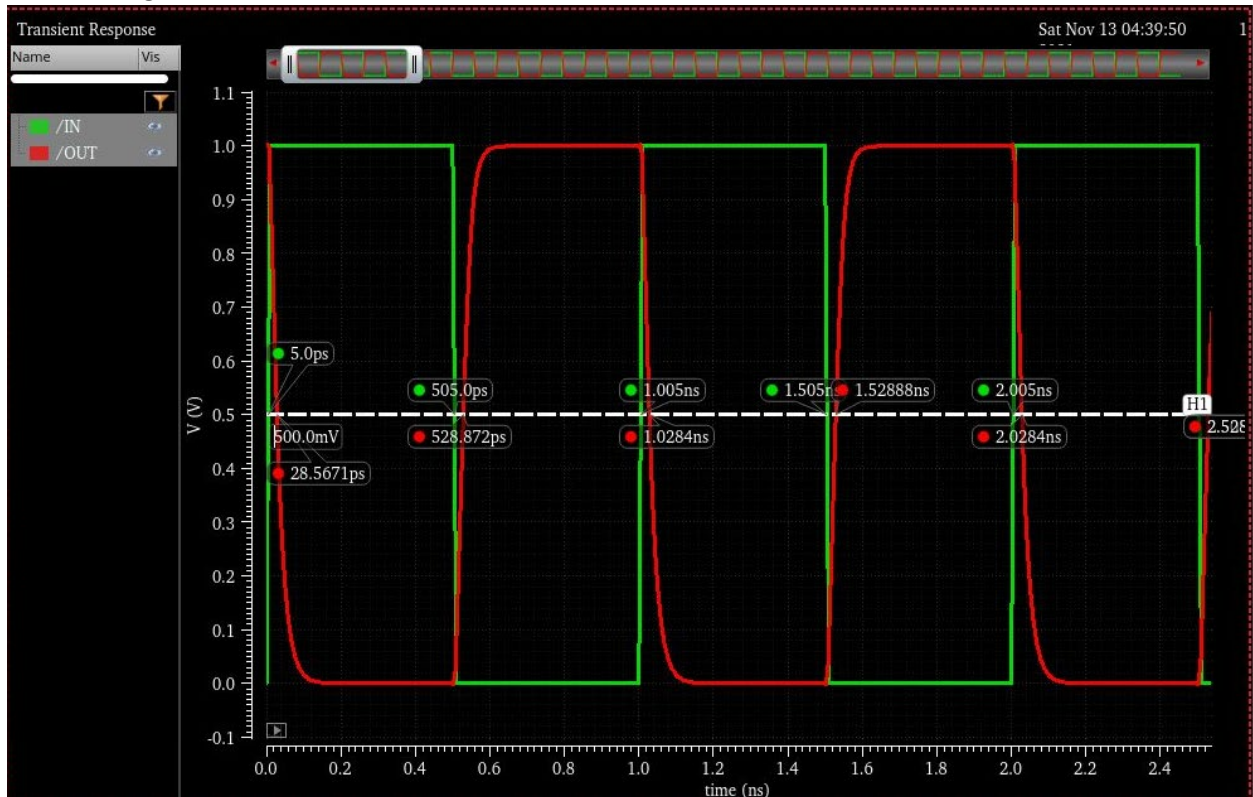


Tau with all parasitics from PEX. $T_{pLH} = 25.875$ ps. $T_{pHL} = 51.17$ ps.

This clearly does not match (not equal ± 5 ps) as specified by the assignment. Widths must be changed. Let's try doubling the width of the NMOS to 4 fingers (default 2):



I also managed to shrink it a little bit more and re-ran with DRC, LVS, and PEX.



Now, $T_{pLH} = 23.872$ ps and $T_{pHL} = 23.4$ ps. They match (equal)!

```

File: NAND3.pex.netlist.NAND3.pxi
Created: Sat Nov 13 04:26:13 2021
* PM NAND3_NET2 N.NET2_MM3_s N.NET2_MM4_d N.NET2_c_7_n VSS PM NAND3_NET2
* PM NAND3_NET3 N.NET3_MM4_s N.NET3_MM5_d N.NET3_c_31_n VSS PM NAND3_NET3
* PM NAND3_OUT N.OUT_MM0_d N.OUT_MM1_d OUT_N.NET3_MM3_d VSS PM NAND3_OUT
* PM NAND3_VSS N.VSS_MM5_s VSS VSS PM NAND3_VSS
cc 1 A N.NET2_c_7_n 9.33263e-19
cc 2 A B 0.00153346f
cc 3 A VDD 6.22307e-19
cc 4 A C 2.6717e-19
cc 5 A OUT 0.00174622f
cc 6 N.NET2_c_7_n B 0.00154486f
cc 7 N.NET2_c_7_n N.NET3_c_31_n 0.0131741f
cc 8 N.NET2_c_7_n OUT 0.014384f
cc 9 B VDD 4.97251e-19
cc 10 B C 0.00165237f
cc 11 B N.NET3_c_31_n 0.00173292f
cc 12 B OUT 4.79865e-19
cc 13 VDD C 5.33372e-19
cc 14 VDD N.NET3_c_31_n 7.09484e-19
cc 15 VDD OUT 0.0120485f
cc 16 C N.NET3_c_31_n 0.00143863f
cc 17 C OUT 5.44083e-19
cc 18 C VSS 0.00152284f
cc 19 N.NET3_c_31_n VSS 0.0130981f
cc 20 OUT VSS 5.75347e-19
* File: NAND3.pex.netlist.pex
Created: Sat Nov 13 04:26:13 2021
Program "Calibre xRC"
Version "v2018.1.36.27"
Nominal Temperature: 25C
Circuit Temperature: 25C
*
8 .subckt PM NAND3_NET2 1 3 7 VSS
9 c4 7 VSS 0.234767f
10 r5 3 7 1.3
11 r6 1 7 1.3
12 .ends
13
14 .subckt PM NAND3_NET3 1 3 7 VSS
15 c5 7 VSS 0.200777f
16 r6 3 7 1.3
17 r7 1 7 1.3
18 .ends
19
20 .subckt PM NAND3_OUT 1 3 5 7 VSS
21 c6 5 VSS 0.190157f
22 r7 5 7 1.3
23 r8 3 5 0.2
24 r9 1 5 0.2
25 .ends
26
27 .subckt PM NAND3_VSS 1 4 VSS
28 c3 4 VSS 0.100484f
29 r4 1 4 0.4
30 .ends
31

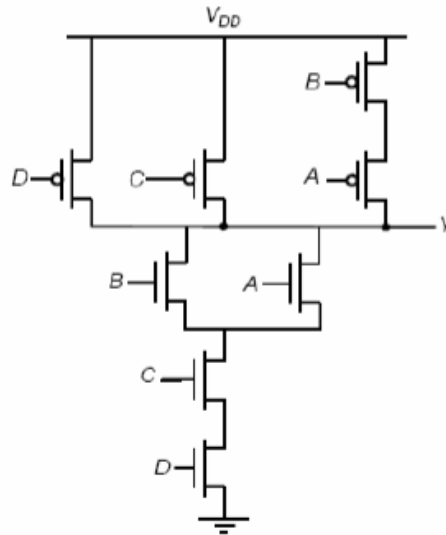
```

PEX Netlist.

Avg worst case delay is: 23.636ps.

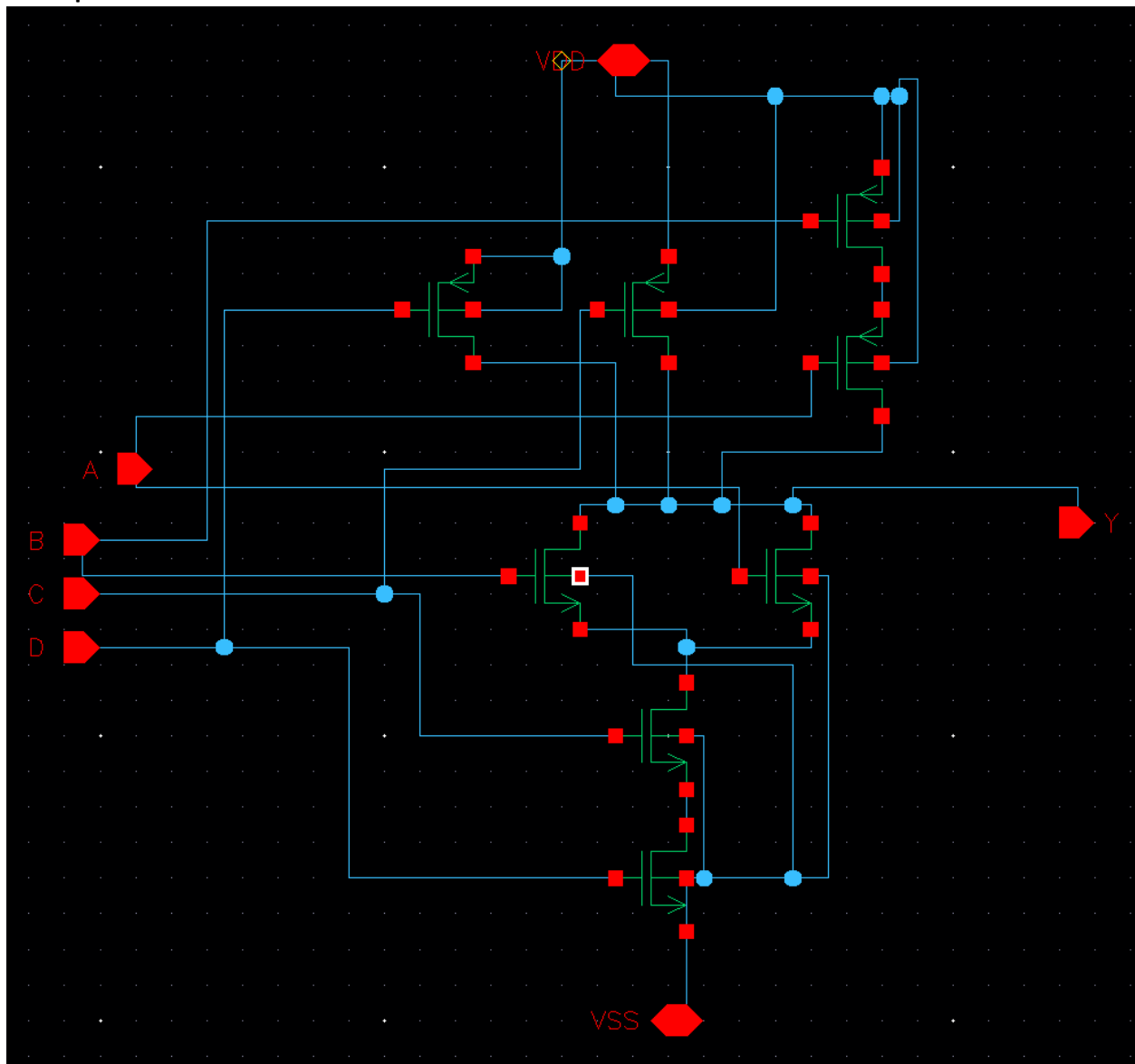
Thus, with area of $0.25978 \text{ } \mu\text{m}^2$, the area x delay is $6.14 \text{ } \mu\text{m}^2 \times \text{ps}$. It is probably possible to shrink the area even further at the cost of repeatedly fixing DRC errors, but since fixing DRC + changing width + refixing DRC already took me tons of hours I'm going to not do that 😊.

2. Sizing and Timing of:



- a. The logic function (Boolean) can be obtained by observing the pull-down NMOS. We see A and B in parallel, followed by a series C and D. Hence: $Y_{\text{bar}} = (A + B)CD$ and $Y = (AB)_{\text{bar}} + C_{\text{bar}} + D_{\text{bar}}$
- b. Sizing can be obtained by finding the worst case, then going off from there. We are told NMOS W/L is 4 lambda and PMOS W/L is 8 lambda.
 - i. NMOS: Worst case is through A or B to C to D. There are three transistors, so all their widths are $4 * 3 = 12$ lambda
 - ii. PMOS: Worst case is through B to A. There are two transistors, so A and B are $8 * 2 = 16$ lambda. Single branch for C and D makes them 8 lambda.
- c. Timing to get worst case tpHL and tpLH:
 - i. tpHL: For high to low, we need the pull-down network to pull from high to low. So, D should be off initially and on afterwards. For the other ones, we want to maximize capacitance and as many to be up to VDD so that discharging takes the longest, so: ABCD = 1010 -> 1011
 - ii. tLH: For low to high, we need the pull-up network to pull from low to high. So, C and D should be on, and either B or A should also be on. This means that the PMOS side is not pulling up initially. As delay propagates, we want the most delay to be at the beginning, so A should be off and B should be on, then go off: ABCD = 0111 -> 0011.
 - iii. Simulation:

15nm pdk circuit:



For the TB images below, V2 pulse (left) and ADE L settings (right):

<i>Ignore</i>	true
DC voltage	0 V
Source type	pulse
<i>Frequency...</i>	
Delay time	0 s
Zero value	0 V
One value	1 V
Period of ...	10n s
Rise time	10p s
Fall time	10p s
<i>Type of rising...</i>	

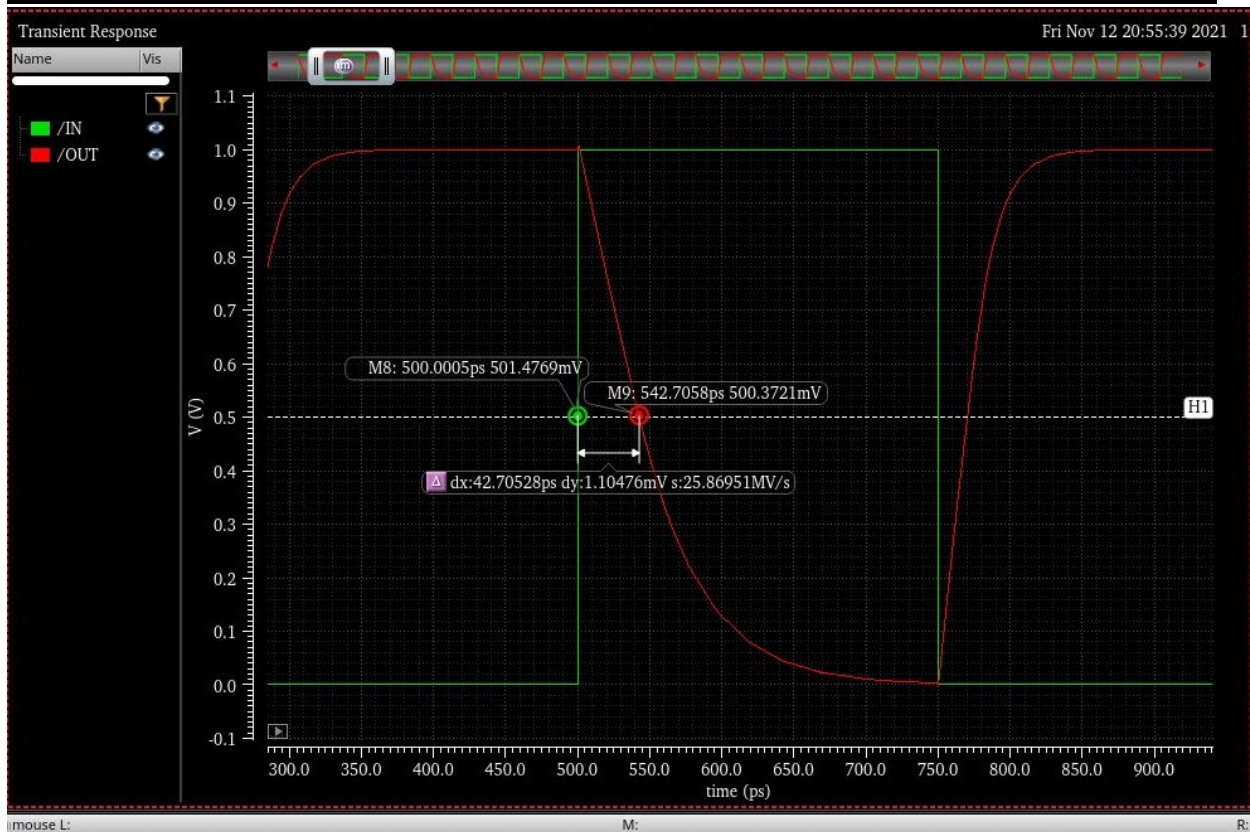
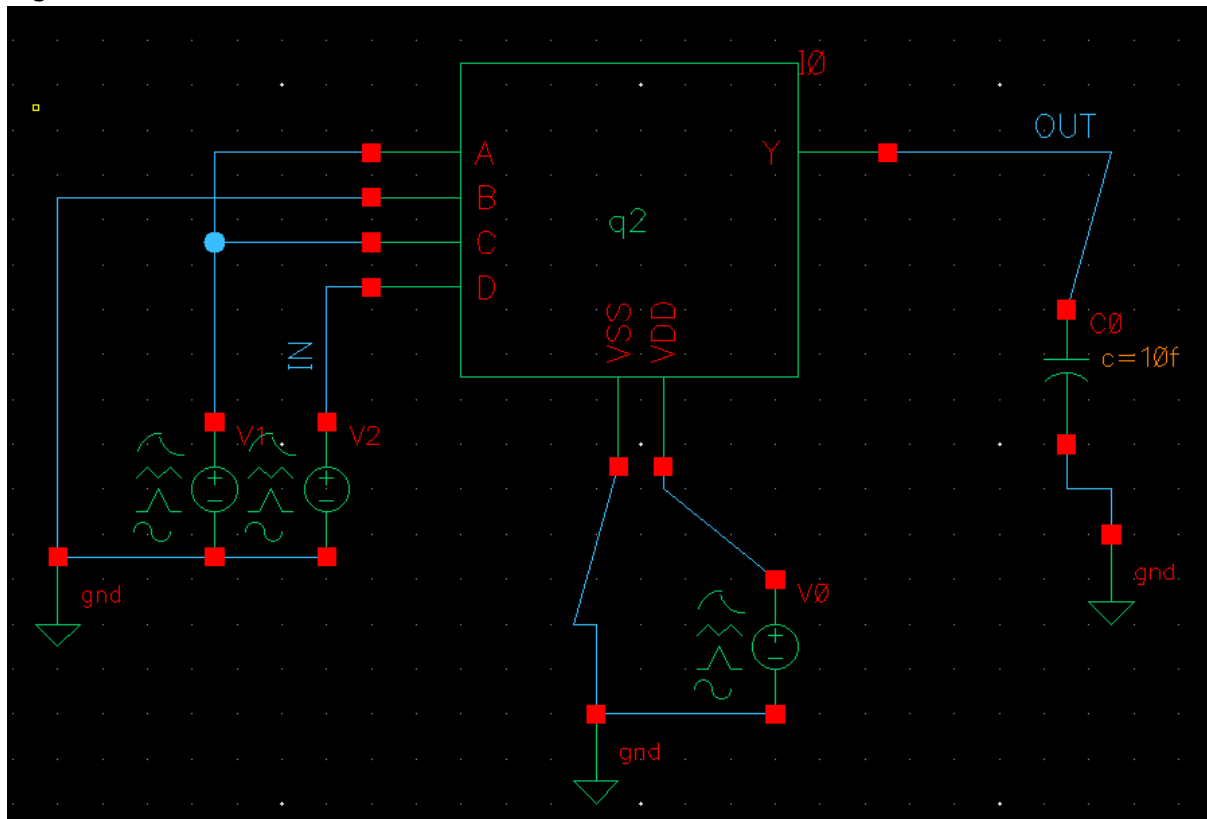
Analyses				
Type	Enable	Arguments		
1 tran	<input checked="" type="checkbox"/>	0 10n moderate		

Outputs				
Name/Signal/Expr	Value	Plot	Save	Save Op
1 IN		<input checked="" type="checkbox"/>	<input type="checkbox"/>	allv
2 OUT		<input checked="" type="checkbox"/>	<input type="checkbox"/>	allv

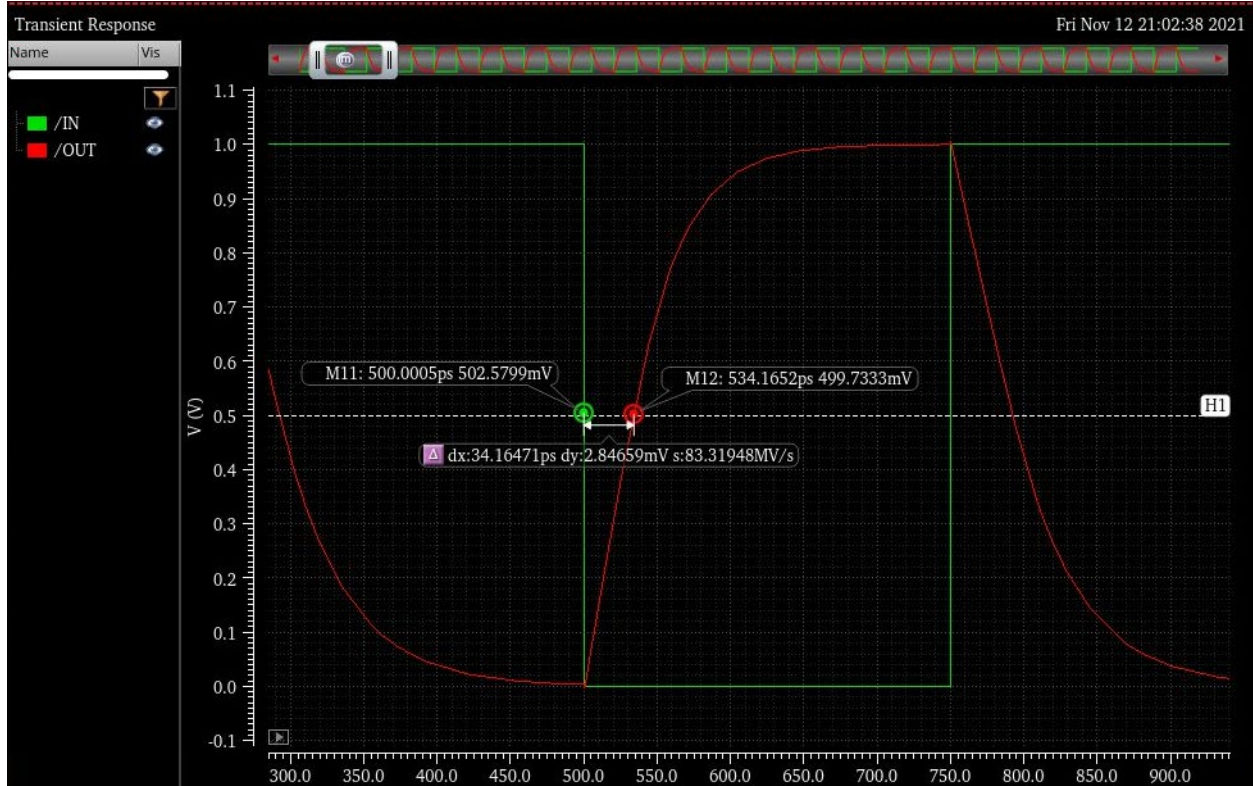
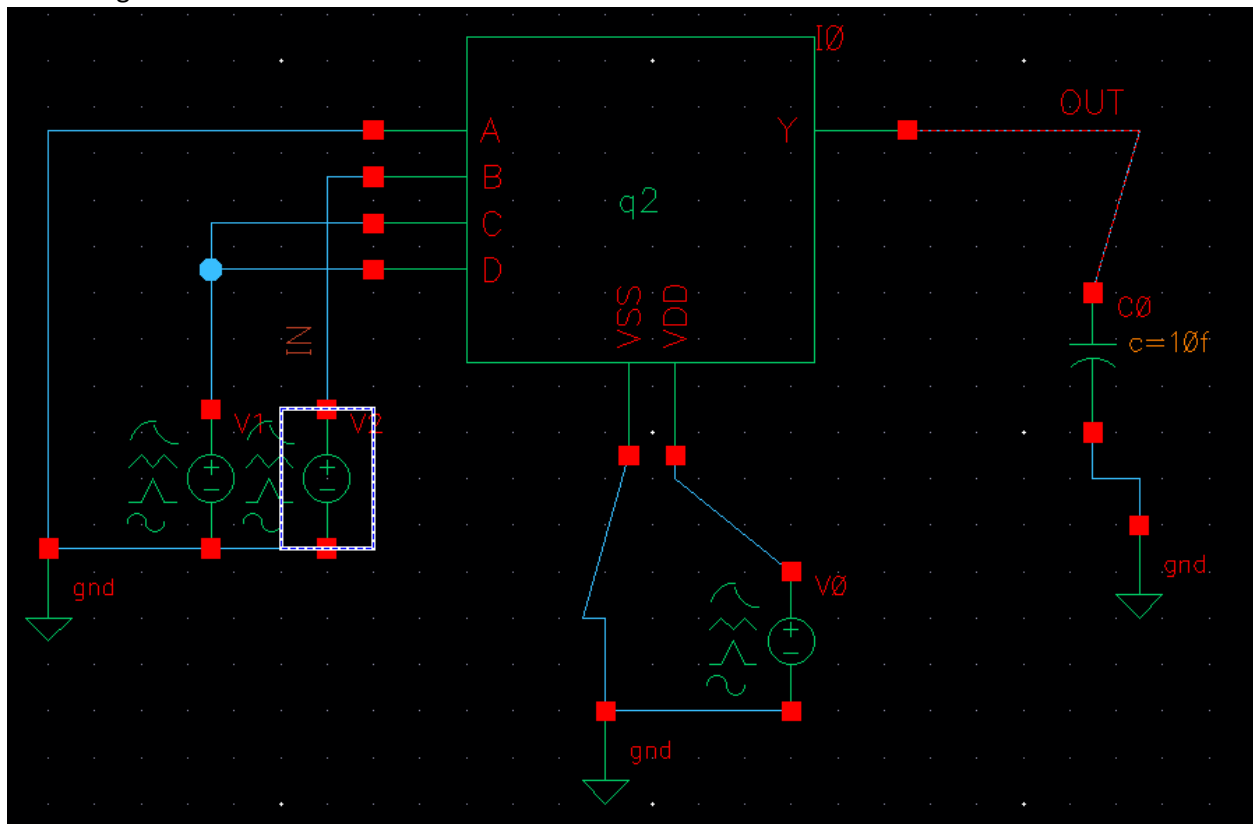
VDD = V1 = V0 = 1V DC

Output cap = 10fF

High to low: ABCD = 1010 -> 1011:



Low to high: ABCD = 0111 -> 0011:



T_{pHL}	T_{pLH}
42.7ps	34.2ps

Schematic Netlist is in Appendix B.

3. Transmission Gates

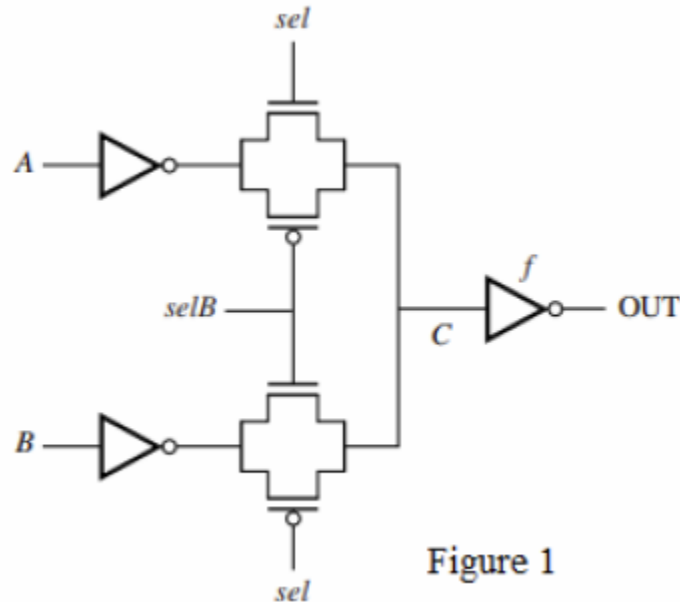
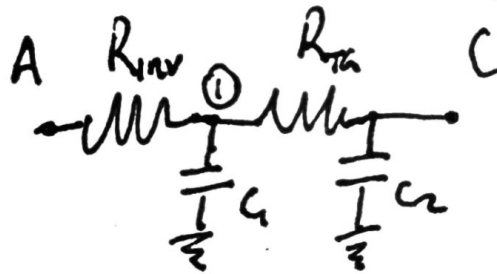


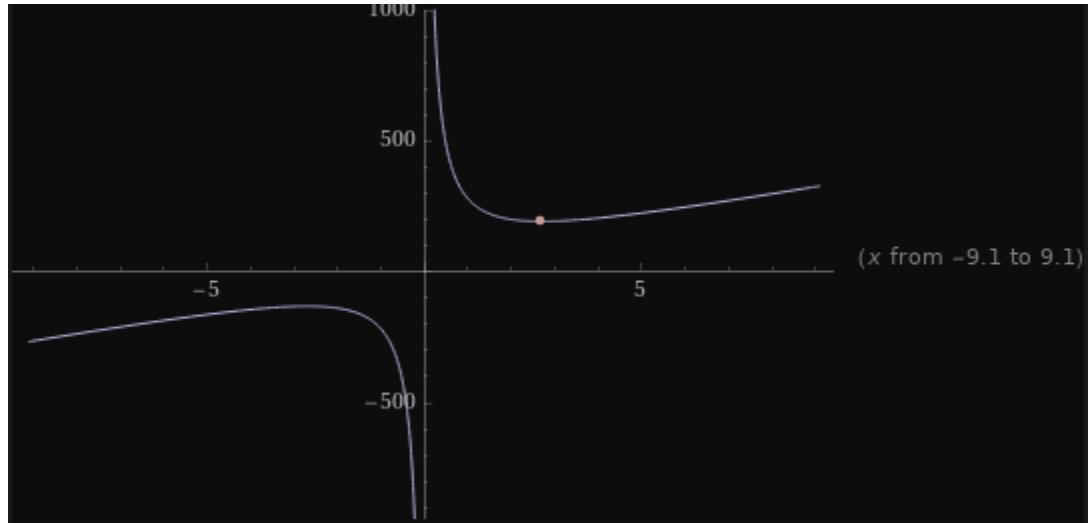
Figure 1

- Expression for output function in terms of A, B, sel, selB. OUT is C'. A' is controlled by sel, B' is controlled by selB. C is A' and sel or B' and selB, so: $OUT = (A \text{sel}') + (B \text{selB}')$
- Equivalent RC circuit model from A to C, given sel is high. A passes through an inverter, then a transmission gate:



-
- Resistances approximation: $R_{inv} = R_{TG} = R_{eqn} (L/W)$, $R_{inv} = R_{TG} = 12.5k$
 $(2/4) = 6.25k$ ohms
- C1 Capacitance ($C_{eff} \rightarrow 1$, $C_g \rightarrow 2$ from formula):
 - $C_{inv} = C_{eff}(4 + 8) = 12C_{eff}$
 - $C_{tg} = C_{eff} * 2 * (4) + C_g (4) = 8C_{eff} + 4C_g$
 - $C1 = C_{inv} + C_{tg} = (20C_{eff} + 4C_g) 0.1 = 2.4$ fF
- C2 Capacitances ($C_{eff} \rightarrow 1$, $C_g \rightarrow 2$ from formula), x multiplier from load inverter (**I use x since I already use f for femto for clarity**):
 - $C_{inv} = C_g(4 + 8) = 12C_g * x$
 - $C_{tg} = C_{eff} * 2 * (4) + C_g (4) = 8C_{eff} + 4C_g$
 - $C2 = C_{inv} + C_{tg} = (8C_{eff} + 12fC_g) 0.1 = (2.4x + 1.6)$ fF

- c. A to C delay. Since the resistances are the same, Elmore delay $t_{\text{elmore}} = RC1 + 2RC2$, where R is 6.25 k ohms and C1, C2 are above. This can simplify to $t_{\text{elmore}} = 6.25k * 2.4f + 2*6.25k*(2.4x + 1.6)f = 15 + 30x + 10.4 \text{ ps} = 25.4 + 30x \text{ ps}$
- d. RC Delay, Load is 50fF, R becomes R/x , and C becomes $(4 + 8) * x * C_{\text{eff}} + 50\text{fF}$. Step (0.7) is used because it's RC delay, which is the most ideal case for the output inverter. So, $t_{rc} = 0.7 * 6.25k/x (50 + 1.2x)f = 4.375 (1.2x + 50) / x \text{ ps}$
- e. Optimal output inverter size to minimize A to OUT: elmore + rc delay and minimize:
 $25.4 + 30x + 4.375 (1.2x + 50) / x$



$$\min \left\{ 25.4 + 30x + \frac{4.375(1.2x + 50)}{x} \right\} \approx 192.669 \text{ at } x \approx 2.70031$$

This is at

So optimal multiplier x (aka f) is 2.7.

ACT009 and NW004A as mentioned can be ignored.

[illegible]

Appendix B: Schematic Netlist of Q2

```
// Generated for: spectre
// Generated on: Nov 13 01:40:18 2021
// Design library name: ELEC402
// Design cell name: q2_tb
// Design view name: schematic
simulator lang=spectre
global 0
include "/CMC/kits/ncsu_pdk/FreePDK15/hspice/models/fet.inc" section=CMG

// Library name: ELEC402
// Cell name: q2
// View name: schematic
subckt q2 A B C D VDD VSS Y
    M3 (Y A net4 VDD) pfet as=6.08e-16 ad=6.08e-16 ps=168n pd=168n m=2 \
        degradation=no
    M2 (net4 B VDD VDD) pfet as=6.08e-16 ad=6.08e-16 ps=168n pd=168n m=2 \
        degradation=no
    M1 (Y C VDD VDD) pfet as=6.08e-16 ad=6.08e-16 ps=168n pd=168n m=2 \
        degradation=no
    M0 (Y D VDD VDD) pfet as=6.08e-16 ad=6.08e-16 ps=168n pd=168n m=2 \
        degradation=no
    M7 (net3 D VSS VSS) nfet as=6.08e-16 ad=6.08e-16 ps=168n pd=168n m=2 \
        degradation=no
    M6 (net2 C net3 VSS) nfet as=6.08e-16 ad=6.08e-16 ps=168n pd=168n m=2 \
        degradation=no
    M5 (Y A net2 VSS) nfet as=6.08e-16 ad=6.08e-16 ps=168n pd=168n m=2 \
        degradation=no
    M4 (Y B net2 VSS) nfet as=6.08e-16 ad=6.08e-16 ps=168n pd=168n m=2 \
        degradation=no
ends q2
// End of subcircuit definition.

// Library name: ELEC402
// Cell name: q2_tb
// View name: schematic
I0 (0 IN net3 net3 net2 0 OUT) q2
C0 (OUT 0) capacitor c=10f
V1 (net3 0) vsource dc=1 type=dc
V0 (net2 0) vsource dc=1 type=dc
V2 (IN 0) vsource dc=0 type=pulse delay=0 val0=1 val1=0 period=500.0p \
    rise=10p fall=10p
simulatorOptions options psfversion="1.1.0" reltol=1e-3 vabstol=1e-6 \
    iabstol=1e-12 temp=27 tnom=27 scalem=1.0 scale=1.0 gmin=1e-12 rforce=1 \
    maxnotes=5 maxwarns=5 digits=5 cols=80 pivrel=1e-3 \
    sensfile="../psf/sens.output" checklimitdest=psf
tran tran stop=10n errpreset=moderate write="spectre.ic" \
    writefinal="spectre.fc" annotate=status maxiters=5
finalTimeOP info what=oppoint where=rawfile
modelParameter info what=models where=rawfile
element info what=inst where=rawfile
outputParameter info what=output where=rawfile
designParamVals info what=parameters where=rawfile
primitives info what=primitives where=rawfile
subckts info what=subckts where=rawfile
saveOptions options save=allpub
```

Appendix C: LVS Report Q1

```
#####
##          ##
##  CALIBRE SYSTEM  ##
##          ##
##    LVS REPORT    ##
##          ##
#####

REPORT FILE NAME:   NAND3.lvs.report
LAYOUT NAME:       /ubc/ece/home/ugrads/m/mchuahua/Cadence_Proj4/svdtb/NAND3.sp ('NAND3')
SOURCE NAME:       /ubc/ece/home/ugrads/m/mchuahua/Cadence_Proj4/NAND3.src.net ('NAND3')
RULE FILE:         /ubc/ece/home/ugrads/m/mchuahua/Cadence_Proj4/_calibrePEX.ru_
CREATION TIME:     Sat Nov 13 04:25:06 2021
CURRENT DIRECTORY: /ubc/ece/home/ugrads/m/mchuahua/Cadence_Proj4
USER NAME:         mchuahua
CALIBRE VERSION:   v2018.1_36.27   Tue Apr 3 12:54:13 PDT 2018


OVERALL COMPARISON RESULTS


# ##### - -
# # # * *
# # # CORRECT # |
# # # # \_/_/
# #####


*****
CELL SUMMARY
*****

Result      Layout      Source
-----
CORRECT      NAND3      NAND3


*****
LVS PARAMETERS
*****

o LVS Setup:

LVS COMPONENT TYPE PROPERTY      element
LVS COMPONENT SUBTYPE PROPERTY  model
// LVS PIN NAME PROPERTY
LVS POWER NAME                  "VDD"
LVS GROUND NAME                 "VSS"
LVS CELL SUPPLY                 NO
LVS RECOGNIZE GATES             ALL
LVS IGNORE PORTS               NO
LVS CHECK PORT NAMES           NO
LVS IGNORE TRIVIAL NAMED PORTS NO
LVS BUILTIN DEVICE PIN SWAP     YES
LVS ALL CAPACITOR PINS SWAPPABLE NO
LVS DISCARD PINS BY DEVICE      NO
LVS SOFT SUBSTRATE PINS         NO
LVS INJECT LOGIC                NO
LVS EXPAND UNBALANCED CELLS     YES
LVS FLATTEN INSIDE CELL        NO
LVS EXPAND SEED PROMOTIONS      NO
LVS PRESERVE PARAMETERIZED CELLS NO
LVS GLOBALS ARE PORTS          YES
LVS REVERSE WL                 NO
LVS SPICE PREFER PINS          NO
LVS SPICE SLASH IS SPACE       YES
LVS SPICE ALLOW FLOATING PINS   YES
// LVS SPICE ALLOW INLINE PARAMETERS
LVS SPICE ALLOW UNQUOTED STRINGS NO
LVS SPICE CONDITIONAL LOD      NO
LVS SPICE CULL PRIMITIVE SUBCIRCUITS NO
// LVS SPICE EXCLUDE CELL SOURCE
// LVS SPICE EXCLUDE CELL LAYOUT
LVS SPICE IMPLIED MOS AREA     NO
// LVS SPICE MULTIPLIER NAME
LVS SPICE OVERRIDE GLOBALS     NO
LVS SPICE REDEFINE PARAM       NO
LVS SPICE REPLICATE DEVICES    NO
LVS SPICE SCALE X PARAMETERS   NO
LVS SPICE STRICT WL            NO
// LVS SPICE OPTION
LVS STRICT SUBTYPES            NO
LVS EXACT SUBTYPES             NO
LAYOUT CASE                    NO
SOURCE CASE                    NO
LVS COMPARE CASE               NO
LVS DOWNCASE DEVICE            NO
LVS REPORT MAXIMUM             50
LVS PROPERTY RESOLUTION MAXIMUM 32
// LVS SIGNATURE MAXIMUM
// LVS FILTER UNUSED OPTION
// LVS REPORT OPTION
LVS REPORT UNITS               YES
// LVS NON USER NAME PORT
// LVS NON USER NAME NET
// LVS NON USER NAME INSTANCE
// LVS IGNORE DEVICE PIN
// LVS PREFER NETS FILTER SOURCE
// LVS PREFER NETS FILTER LAYOUT

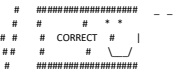
// Reduction

LVS REDUCE SERIES MOS          YES
LVS REDUCE PARALLEL MOS        YES
LVS REDUCE SEMI SERIES MOS     YES
```

LVS REDUCE SPLIT GATES YES
LVS REDUCE PARALLEL BIPOLAR YES
LVS REDUCE SERIES CAPACITORS YES
LVS REDUCE PARALLEL CAPACITORS YES
LVS REDUCE SERIES RESISTORS YES
LVS REDUCE PARALLEL RESISTORS YES
LVS REDUCE PARALLEL DIODES YES
LVS REDUCTION PRIORITY PARALLEL

LVS SHORT EQUIVALENT NODES NO

CELL COMPARISON RESULTS (TOP LEVEL)



LAYOUT CELL NAME: NAND3
SOURCE CELL NAME: NAND3

INITIAL NUMBERS OF OBJECTS

	Layout	Source	Component Type
Ports:	6	6	
Nets:	10	10	
Instances:	3	3	MN (4 pins)
	3	3	MP (4 pins)
Total Inst:	6	6	

NUMBERS OF OBJECTS AFTER TRANSFORMATION

	Layout	Source	Component Type
Ports:	6	6	
Nets:	8	8	
Instances:	1	1	NAND3 (4 pins) output input input input
Total Inst:	1	1	

INFORMATION AND WARNINGS

	Matched Layout	Matched Source	Unmatched Layout	Unmatched Source	Component Type
Ports:	6	6	0	0	
Nets:	8	8	0	0	
Instances:	1	1	0	0	NAND3
Total Inst:	1	1	0	0	

o Initial Correspondence Points:

Ports: VDD VSS A B C OUT

SUMMARY

Total CPU Time: 16 sec
Total Elapsed Time: 20 sec